

ABSTRACT OF THE DISCLOSURE

A magnetic memory device includes a memory cell which has a first wiring line composed of a first wiring layer, a second wiring line composed of a second wiring layer and provided above or below the first wiring line so as to cross the first wiring line, and a magnetoresistive effect element device provided in a position where the first wiring line and the second wiring line cross each other. The device further includes a peripheral circuit which includes a third wiring line provided around the memory cell and composed of the first wiring layer, a fourth wiring line provided above or below the third wiring line and composed of the second wiring layer, and at least one magnetic layer forming the magnetoresistive effect element device and provided between the third wiring line and the fourth wiring line.